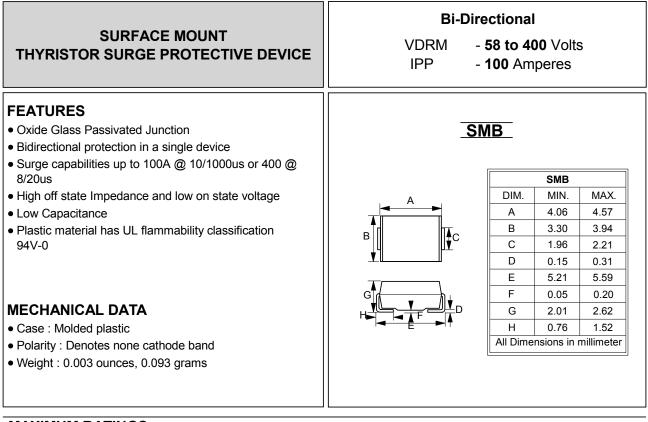
LITE ON SEMICONDUCTOR

TB0640HL thru TB4600HL



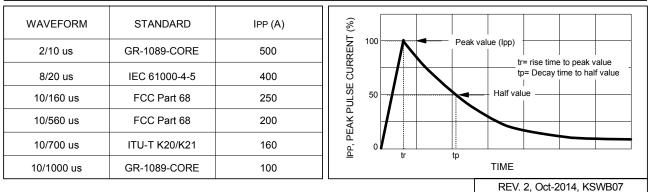
MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	VALUE	UNIT
Non-repetitive peak impulse current @ 10/1000us		100	Α
Non-repetitive peak On-state current @ 8.3ms (one half cycle)	ITSM	50	A
Junction temperature range	TJ	-40 to +150	°C
storage temperature range	TSTG	-55 to +150	°C

THERMAL RESISTANCE

CHARACTERISTICS	SYMBOL	VALUE	UNIT
Junction to leads	Rth(J-L)	20	°C/W
Junction to ambient on print circuit (on recommended pad layout)	Rth(J-A)	100	°C/W
Typical positive temperature coefficient for brekdown voltage	∆Vbr/∆Tj	0.1	%/°C

MAXIMUM RATED SURGE WAVEFORM

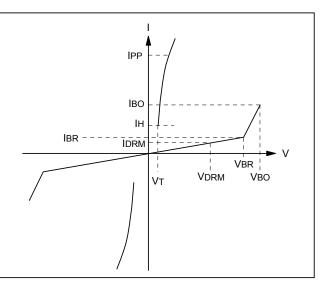




@ TA= 25℃ unless otherwise specified

PARAMETER	MARKING CODE	RATED REPETITIVE OFF-STATE VOLTAGE	OFF-STATE LEAKAGE CURRENT @ VDRM	BREAKOVER VOLTAGE	ON-STATE VOLTAGE @ IT=1.0A		KOVER RENT	-	DING RENT	OFF-STATE CAPACITANCE		
SYMBOL		VDRM	IDRM	Vво	Vт	le	30	I	н	Co		
UNITS		v	uA	v	v	mA		mA		mA mA pF		pF
LIMIT		Мах	Мах	Мах	Мах	Min	Max	Min	Мах	Тур		
TB0640HL	T064HL	58	5	77	3.5	50	800	150	800	40		
TB0720HL	T072HL	65	5	88	3.5	50	800	150	800	40		
TB0900HL	T090HL	75	5	98	3.5	50	800	150	800	40		
TB1100HL	T110HL	90	5	130	3.5	50	800	150	800	40		
TB1300HL	T130HL	120	5	160	3.5	50	800	150	800	40		
TB1500HL	T150HL	140	5	180	3.5	50	800	150	800	40		
TB1800HL	T180HL	170	5	220	3.5	50	800	150	800	40		
TB2300HL	T230HL	190	5	265	3.5	50	800	150	800	40		
TB2600HL	T260HL	220	5	300	3.5	50	800	150	800	40		
TB3100HL	T310HL	275	5	350	3.5	50	800	150	800	40		
TB3500HL	T350HL	320	5	400	3.5	50	800	150	800	40		
TB4000HL	T400HL	360	5	450	3.5	50	800	150	800	40		
TB4600HL	T460HL	400	5	520	3.5	50	800	150	800	40		

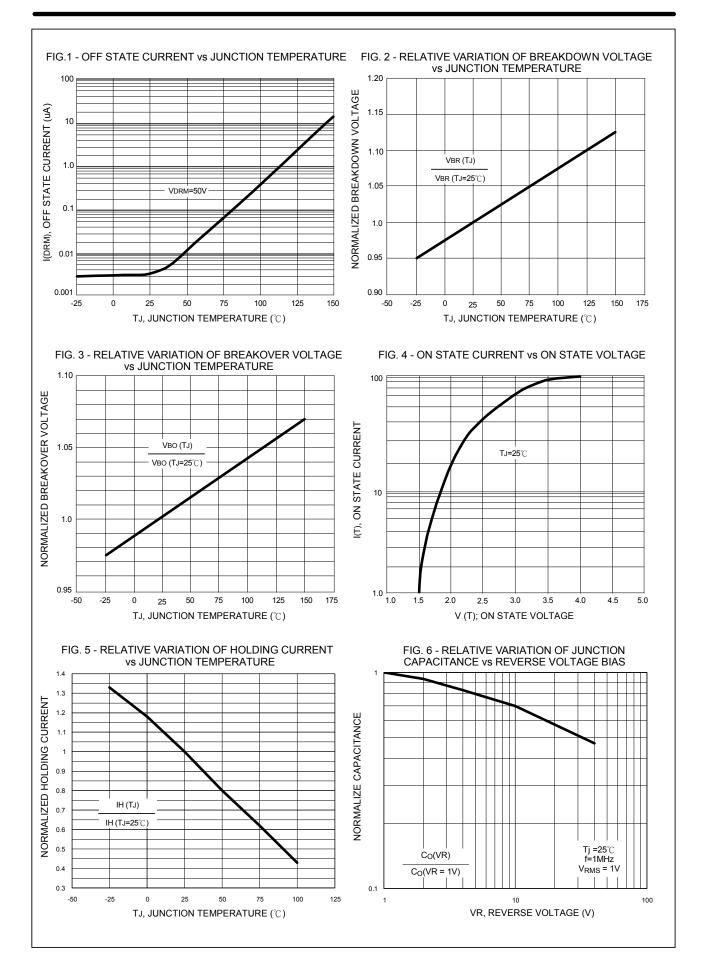
SYMBOL	PARAMETER			
VDRM	Stand-off Voltage			
IDRM	Leakage current at stand-off voltage			
VBR	Breakdown voltage			
IBR	Breakdown current			
Vво	Breakover voltage			
IBO	Breakover current			
Iн	Holding current	Note: 1		
VT	On state voltage			
IPP	Peak pulse current			
Со	Off state capacitance	Note: 2		



NOTES: 1. IH > (VL/RL) If this criterion is not obeyed, the TSPD Triggers but does not return correctly to high-resistance state. The Surge recovery time does not exceed 30ms.

2. Off-state capacitance measured at f=1.0MHz; 1.0VRMS signal; VR=2VDC bias.

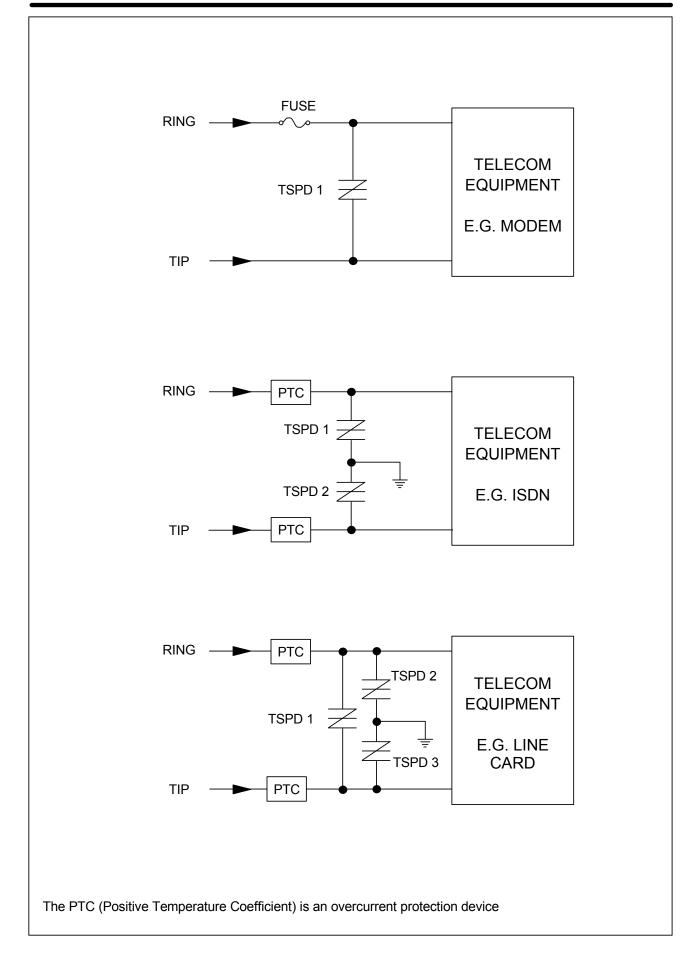
RATING AND CHARACTERISTICS CURVES TB0640HL thru TB4600HL



LITEON

TYPICAL CIRCUIT APPLICATIONS TB0640HL thru TB4600HL







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